MOTOROLA
SEMICONDUCTOR TECHNICAL DATA

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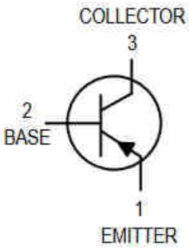
Amplifier Transistors
PNP Silicon

BC212,B
BC213
BC214



CASE 29–04, STYLE 17
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	BC 212	BC 213	BC 214	Unit
Collector–Emitter Voltage	V_{CEO}	–50	–30	–30	Vdc
Collector–Base Voltage	V_{CBO}	–60	–45	–45	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0			Vdc
Collector Current — Continuous	I_C	–100			mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8			mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.0 8.0			Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150			°C

BC212, BC212B, BC213

Amplifier Transistors
PNP Silicon

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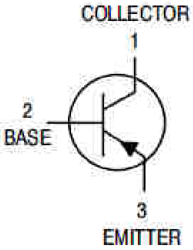

TO–92
CASE 29
STYLE 17

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}		Vdc
BC212		–50	
BC213		–30	
Collector-Base Voltage	V_{CBO}		Vdc
BC212		–60	
BC213		–45	
Emitter-Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current – Continuous	I_C	–100	mAdc
Total Device Dissipation	P_D		
@ T_A = 25°C		350	mW
Derate above 25°C		2.8	mW/°C
Total Device Dissipation	P_D		
@ T_C = 25°C		1.0	Watts
Derate above 25°C		8.0	mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	°C